L Number	Hits	Search Text	DB	Time stamp
1	914	(MINO near1 NORIHISA).in. (KAWAWAKE near1	USPAT;	2004/10/04 10:45
		YASUHIRO).in. (MORITA near1 KIYOYUKI).in. (YOSHII near1	US-PGPUB;	
•		SHIGEO).in. (MURAKAMI near1 MUTUAKI).in. (KUSUMOTO	EPO; JPO;	
İ		near1 OSAMU).in.	DERWENT:	
			IBM_TDB	
2	213	((MINO near1 NORIHISA).in. (KAWAWAKE near1	USPAT:	2004/10/04 10:59
		YASUHIRO).in. (MORITA near1 KIYOYUKI).in. (YOSHII near1	US-PGPUB:	
		SHIGEO).in. (MURAKAMI near1 MUTUAKI).in. (KUSUMOTO	EPO; JPO;	
]		near1 OSAMU).in.) and organic	DERWENT;	
			IBM TDB	
3	30	(((MINO near1 NORIHISA).in. (KAWAWAKE near1	USPAT:	2004/10/04 10:56
		YASUHIRO).in. (MORITA near1 KIYOYUKI).in. (YOSHII near1	US-PGPUB:	2004/10/04 10:50
ĺ		SHIGEO).in. (MURAKAMI near1 MUTUAKI).in. (KUSUMOTO	EPO; JPO;	
		near1 OSAMU).in.) and organic) and (assemble assembly	DERWENT;	
		self\$1assembly self\$1assembled array)	IBM TDB	
4	3	6730395.pn.	_	2004/40/04 40 57
	Ŭ	67 00000.рп.	USPAT;	2004/10/04 10:57
			US-PGPUB;	
			EPO; JPO;	
İ			DERWENT;	
5	13	/"6720205" "20020176057" "6502000" "650120 4" "0502507"	IBM_TDB	
	13	("6730395" "20020176957" "6593000" "6521334" "6503567"	USPAT;	2004/10/04 10:59
		"6410152" "6342716" "6277444" "5871815" "5515190"	US-PGPUB	
6	040000	"6159620" "6232777" "6341053").pn.		
0	613089	(M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:11
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
ļ		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.	DERWENT;	
<b>-</b>			IBM_TDB	
7	378	((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:50
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB:	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT:	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
		(ordered adj particles))		
8	243	(((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:31
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB:	200 1/10/04 11:01
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
}		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
	1	(ordered adj particles))) and (nano nano\$1particle\$1 particle)	10101_100	
9	111	(((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:31
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB:	2004/10/04 11:31
		resistance) (magnetic adj (head element memory sensor	,	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	EPO; JPO;	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	DERWENT;	
	ŀ	(ordered adj particles))) and (functional adj group)	IBM_TDB	
10	304		LICDAT	00044000
	504	(((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:31
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
1		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	İ
		(ordered adj particles))) and (polymer mono\$1mer\$1 organic)		

11	92	((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:44
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
		(ordered adj particles))) and (nano nano\$1particle\$1 particle))		
		and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J		
		magneto\$1resistive magneto\$1resistance (magneto adj		
	Ì	resistive) (magneto adj resistance) (magnetic adj (head		
		element memory sensor apparatus)) spin\$1valve\$1 (spin adj		
		valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4)		
	1	(ordered adj array) (ordered adj particles))) and (functional adj		•
		group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J		
		magneto\$1resistive magneto\$1resistance (magneto adj	1	
		resistive) (magneto adj resistance) (magnetic adj (head		
		element memory sensor apparatus)) spin\$1valve\$1 (spin adj		İ
		valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4)		
		(ordered adj array) (ordered adj particles))) and (polymer		
		mono\$1mer\$1 organic))		
12	6189	black.in.	USPAT;	2004/10/04 11:44
			US-PGPUB:	
			EPO; JPO;	
			DERWENT:	
			IBM TDB	
13	478	black.in. and (nano nano\$1particle\$1 particle)	USPAT;	2004/10/04 11:45
			US-PGPUB;	·
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
14	107	(black.in. and (nano nano\$1particle\$1 particle)) and magnetic	USPAT;	2004/10/04 11:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	3185	((self\$1assembl\$4 (self adj assembl\$4)) adj array) (ordered	USPAT;	2004/10/04 11:52
		adj array) (ordered adj particles)	US-PGPUB;	
			EPO; JPO;	
ļ			DERWENT;	
4.0			IBM_TDB	
16	72	(((self\$1assembl\$4 (self adj assembl\$4)) adj array) (ordered	USPAT;	2004/10/04 11:52
		adj array) (ordered adj particles)) and (organic near4	US-PGPUB;	
		functional)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

17		((((self\$1assembl\$4 (self adj assembl\$4)) adj array) (ordered adj array) (ordered adj particles)) and (organic near4 functional)) not ((("6730395" "20020176957" "6593000" "6521334" "6503567" "6410152" "6342716" "6277444" "5871815" "5515190" "6159620" "6232777" "6341053").pn.) ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer mono\$1mer\$1 organic))) ((black.in. and (nano nano\$1particle\$1 particle)) and magnetic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 12:01
18	7	("6162532" "20020022111" "6730395" "6420086" "4618509" "5670257" "6103868").pn.	USPAT; US-PGPUB	2004/10/04 12:02
19	19	(("6730395" "20020176957" "6593000" "6521334" "6503567" "6410152" "6342716" "6277444" "5871815" "5515190" "6159620" "6232777" "6341053").pn.) (("6162532" "20020022111" "6730395" "6420086" "4618509" "5670257" "6103868").pn.)	USPAT; US-PGPUB	2004/10/04 12:02